

IN THE CLAIMS:

Claims 1-10 (canceled)

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11. (new): A multiwall carbon nanotube having an outer wall and at least one inner wall, wherein only the outer wall is oxidized and the inner wall or walls are not oxidized.

12. (new): The multiwall carbon nanotube as claimed in Claim 1, further comprising a substrate on which the multiwall carbon nanotube is bound.

13. (new): The multiwall carbon nanotube as claimed in Claim 2, further comprising an electronic component comprising the substrate.

14. (new): A process for oxidizing only the outer wall of a multiwall carbon nanotube, comprising:

providing a multiwall carbon nanotube;

subjecting the multiwall carbon nanotube to oxidation; and

isolating the multiwall carbon nanotube which has been isolate in this manner.

15. (new): The process claimed in Claim 4, further comprising carrying out the oxidation by reaction with an acid selected from the group consisting of nitric acid, sulfuric acid, chromic acid, Caro's acid, perchloric acid, iodic acid, and an organic peracid.

16. (new): The process claimed in Claim 5, wherein sulfuric acid is used as a mixture with hydrogen peroxide.

17. (new): The process as claimed in one of Claims 4 to 6, further comprising carrying out the oxidation of the outer wall of the multiwall carbon nanotube at a temperature up to the boiling point of the respective reaction mixture.

18. (new): A multiwall carbon nanotube doped with boron nitride having an outer wall and at least one inner wall, wherein only the outer wall is oxidized and the inner wall or walls are not oxidized.

19. (new): The multiwall carbon nanotube doped with boron nitride as claimed in Claim 8, further comprising a substrate on which the multiwall carbon nanotube doped with boron nitride is bound.

20. (new): The multiwall carbon nanotube doped with boron nitride as claimed in Claim 9, further comprising an electronic component comprising the substrate.

21. (new): A process for oxidizing only the outer wall of a multiwall carbon nanotube doped with boron nitride, comprising:

providing a multiwall carbon nanotube doped with boron nitride;

subjecting the multiwall carbon nanotube doped with boron nitride to oxidation; and

isolating the multiwall carbon nanotube doped with boron nitride which has been treated in this manner.

22. (new): The process claimed in Claim 11, further comprising carrying out the oxidation by reaction with an acid selected from the group consisting of nitric acid, sulfuric acid, chromic acid, Caro's acid, perchloric acid, iodic acid, and an organic peracid.

23. (new): The process claimed in Claim 12, wherein sulfuric acid is used as a mixture with hydrogen peroxide.

24. (new): The process as claimed in one of Claims 11 to 13, further comprising carrying out the oxidation of the outer wall of the multiwall carbon nanotube doped with boron nitride at a temperature up to the boiling point of the respective reaction mixture.